NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRAL1720-5** is Designed for Class C, Common Base Wideband Large Signal Amplifier Applications up to 2.0 GHz.

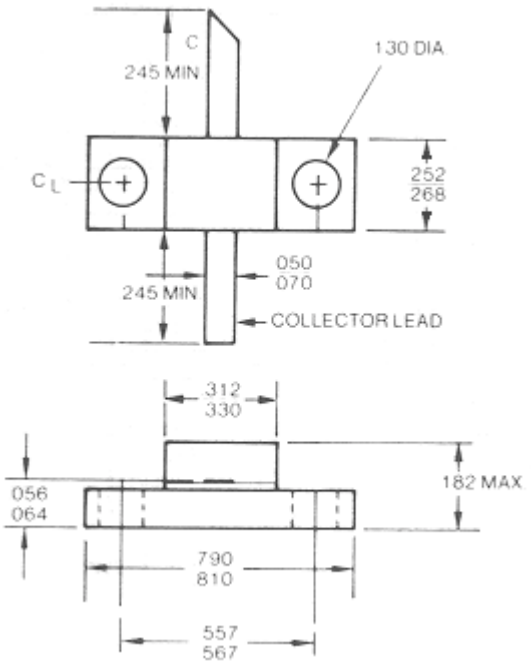
FEATURES:

- Diffused Ballast Resistors.
- Internal Matching Network
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	1.0 A (CONT)
V_{CES}	42 V
V_{EBO}	3.5 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	8.0 °C/W

PACKAGE STYLE 400 4L FLG



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 40 mA	42			V
BV_{EBO}	I_E = 0.5 mA	3.5			V
I_{CBO}	V_{CB} = 22 V			1.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 200 mA	10		100	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			8.0	pF
G_{PB} η_C	V_{CE} = 22 V P_{out} = 5.0 W f = 1.7 GHz & 2.0 GHz	6.5 40			dB %

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Specifications are subject to change without notice.